

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A semiconductor manufacturing device comprising a processing chamber including a susceptor for supporting a substrate, wherein the susceptor has a main body containing a wall forming inside an electrode arranging space substantially flat and parallel to the substrate and multiple pillars joining the bottom and ceiling of the wall; and a high-frequency electrode having at least one insertion hole for receiving at least one of the multiple pillars, the high-frequency electrode being installed with a gap between the electrode and the at least one of the ~~pillar~~ multiple pillars within the electrode arranging space.

Claim 2 (Original): A semiconductor manufacturing device according to claim 1, wherein the distance from the high frequency electrode to the supporting surface for supporting the substrate provided on the susceptor surface higher than the high-frequency electrode, is set smaller than the distance from the high-frequency electrode to the susceptor rear surface lower than the high-frequency electrode.

Claim 3 (Original): A semiconductor manufacturing device according to claim 1 or claim 2, wherein the electrode arranging space is insulated from the atmosphere in the processing chamber and is connected to the atmosphere outside the processing chamber.

Claim 4 (Previously Presented): A semiconductor manufacturing device according to claim 1 or claim 2, wherein the high-frequency electrode is comprised of a plate formed with insertion holes where the pillars are inserted.

Claim 5 (Currently Amended): A method for manufacturing semiconductor devices comprising the steps of:

supporting a substrate on a susceptor installed in a processing chamber,

supplying and exhausting a process gas to and from the processing chamber, and

performing plasma processing of the substrate by the susceptor having a main body containing a wall forming inside an electrode arranging space substantially flat and parallel to the substrate and multiple pillars joining the bottom and ceiling of the wall; and a high-frequency electrode having at least one insertion hole for receiving at least one of the multiple pillars, the high-frequency electrode being installed with a gap between the electrode and the at least one of the pillar multiple pillars within the electrode arranging space.

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